

Page 5, replace the paragraph, beginning on line 10, as

follows:

B2
--It is a further object of the present invention to provide a novel method of treating a semiconductor wafer surface suppressing oxidation of a copper-region of the surface thereof even if the semiconductor wafer is exposed to the atmosphere.--;

replace the paragraph, beginning on line 24, bridging pages 5 and 6, as follows:

B3
--It is a further object of the present invention to provide a novel method of forming a semiconductor device suppressing oxidation of a copper-region of the surface thereof even if the semiconductor wafer is exposed to the atmosphere.--.

Page 10, replace the paragraph, beginning on line 24, bridging pages 10 and 11, as follows:

B4
--It is necessary to prevent the above formations of the CuOx film and the hillock, even if the semiconductor wafer is exposed to the atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface. Namely, it is necessary to prevent any oxidation of the copper region or the copper interconnection surface on the semiconductor wafer surface even if the semiconductor wafer is exposed to the atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface.--.

Page 11, replace the paragraph, beginning on line 8, as follows:

65 --In accordance with the present invention, an anti-corrosion treatment is carried out by exposing the surface of the semiconductor wafer to a solution containing an anti-corrosive agent thereby to form an anti-corrosive film before a copper-diffusion stopper insulating film is then formed over the surface of the semiconductor substrate, so that the anti-corrosive film prevents the semiconductor wafer surface from any oxidation during when the semiconductor wafer surface is exposed to the atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface. As a result, it is possible to prevent the above formations of the CuOx film and the hillock, even if the semiconductor wafer is exposed to the atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface. Namely, it is possible to prevent any oxidation of the copper region or the copper interconnection surface on the semiconductor wafer surface even if the semiconductor wafer is exposed to the atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface.--.

Page 15, replace the paragraph, beginning on line 16, bridging pages 15 and 16, as follows:

66 --In accordance with the present invention, an anti-corrosion treatment is carried out by exposing the surface of the semiconductor wafer to a solution containing an anti-corrosive agent thereby to form an anti-corrosive film before a copper-

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end

diffusion stopper insulating film is then formed over the surface of the semiconductor substrate, so that the anti-corrosive film prevents the semiconductor wafer surface from any oxidation during when the semiconductor wafer surface is exposed to the atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface. As a result, it is possible to prevent the above formations of the CuOx film and the hillock, even if the semiconductor wafer is exposed to the atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface. Namely, it is possible to prevent any oxidation of the copper region or the copper interconnection surface on the semiconductor wafer surface even if the semiconductor wafer is exposed to the atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface.--.

Page 20, replace the paragraph, beginning on line 3, as follows:

b7

--In accordance with the present invention, an anti-corrosion treatment is carried out by exposing the surface of the semiconductor wafer to a solution containing an anti-corrosive agent thereby to form an anti-corrosive film before a copper-diffusion stopper insulating film is then formed over the surface of the semiconductor substrate, so that the anti-corrosive film prevents the semiconductor wafer surface from any oxidation during when the semiconductor wafer surface is exposed to the

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atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface. As a result, it is possible to prevent the above formations of the CuOx film and the hillock, even if the semiconductor wafer is exposed to the atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface. Namely, it is possible to prevent any oxidation of the copper region or the copper interconnection surface on the semiconductor wafer surface even if the semiconductor wafer is exposed to the atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface.--.

Page 24, replace the paragraph, beginning on line 20, bridging pages 24 and 25, as follows:

B8

--In accordance with the present invention, an anti-corrosion treatment is carried out by exposing the surface of the semiconductor wafer to a solution containing an anti-corrosive agent thereby to form an anti-corrosive film before a copper-diffusion stopper insulating film is then formed over the surface of the semiconductor substrate, so that the anti-corrosive film prevents the semiconductor wafer surface from any oxidation during when the semiconductor wafer surface is exposed to the atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface. As a result, it is possible to prevent the above formations of the CuOx film and the hillock, even if the semiconductor wafer is exposed to the

atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface. Namely, it is possible to prevent any oxidation of the copper region or the copper interconnection surface on the semiconductor wafer surface even if the semiconductor wafer is exposed to the atmosphere before the copper diffusion stopper insulating film is formed over the semiconductor wafer surface.--.

B8
enc

Page 30, replace the paragraph, beginning on line 18, as follows:

--In accordance with the present invention, the anti-corrosion treatment is carried out by use of the anti-corrosive solution containing 1% of benzotriazole. The semiconductor wafer is rotated while receiving a supply of benzotriazole containing anti-corrosive solution at a flow rate of 1 liter per one minute for 10 seconds to form the anti-corrosive film on the surface of the semiconductor wafer 1.--.

B9

Page 48, replace the paragraph, beginning on line 10, bridging pages 48 and 49, as follows:

--In accordance with the present invention, an anti-corrosion treatment is carried out by exposing the surface of the semiconductor wafer to a solution containing an anti-corrosive agent thereby to form an anti-corrosive film before a copper-diffusion stopper insulating film is then formed over the surface of the semiconductor substrate, so that the anti-corrosive film prevents the semiconductor wafer surface from any oxidation

B10